DFM500NXM33-TS000

Fast Recovery Diode Module

DS6099-1 May 2013 (LN30466)

FEATURES

- Low Reverse Recovery Charge
- High Switching Speed
- Low Forward Volt Drop
- Isolated AlSiC Base With AlN Substrates
- High Current Density Enhanced DMOS
- Dual Diodes Can Be Paralleled For 1000A Rating
- Low FIT Rate

APPLICATIONS

- Chopper Diodes
- Boost and Buck Converters
- Free-wheel Circuits
- Motor Drives
- Resonant Converters
- Induction Heating
- Multi-level Switch Inverters

The DFM500NXM33-TS000 is a dual 3300V, fast recovery diode (FRD) module. Designed for low power loss, the module is suitable for a variety of high voltage applications in motor drives and power conversion.

Fast switching times and low reverse recovery losses allow high frequency operation, making the device suitable for the latest drive designs employing PWM and high frequency switching.

The module incorporates an electrically isolated base plate and low inductance construction enabling circuit designers to optimise circuit layouts and utilise grounded heat sinks for safety.

ORDERING INFORMATION

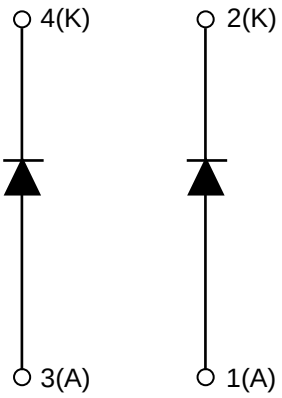
Order As:

DFM500NXM33-TS000

Note: When ordering, please use the complete part number

KEY PARAMETERS

V_{RRM}		**3300V**
V_F	**(typ)**	**2.4V**
I_F	**(max)**	**500A**
I_{FM}	**(max)**	**1000A**



External connection required for a single 2000A diode

Fig. 1 Circuit configuration

Outline type code: N

(See Fig. 7 for further information)

Fig. 2 Package

ABSOLUTE MAXIMUM RATINGS

Stresses above those listed under 'Absolute Maximum Ratings' may cause permanent damage to the device. In extreme conditions, as with all semiconductors, this may include potentially hazardous rupture of the package. Appropriate safety precautions should always be followed. Exposure to Absolute Maximum Ratings may affect device reliability.

T_{case} = 25°C unless stated otherwise

Symbol	Parameter	Test Conditions	Max.	Units
V_{RRM}	Repetitive peak reverse voltage	T_j = 150°C	3300	V
I_F	Forward current (per arm)	DC, T_{case} = 90°C	500	A
I_{FM}	Max. forward current	T_{case} = 135°C, t_p = 1ms	1000	A
I^2t	I^2t value fuse current rating	V_R = 0, t_p = 10ms, T_j = 150°C	80	kA^2s
P_{max}	Max. power dissipation	T_{case} = 25°C, T_j = 150°C	2.6	KW
V_{isol}	Isolation voltage – per module	Commoned terminals to base plate. AC RMS, 1 min, 50Hz	6000	V
Q_{PD}	Partial discharge – per module	IEC1287, V_1 = 3500V, V_2 = 2600V, 50Hz RMS	10	pC
$V_{RRM\ DC}$	DC Voltage stability	25°C at sea level, 100 FITs	2100	V

THERMAL AND MECHANICAL RATINGS

Internal insulation material: AlN

Baseplate material: AlSiC

Creepage distance: 33mm

Clearance: 20mm

CTI (Comparative Tracking Index): >600

Symbol	Parameter	Test Conditions	Min	Typ.	Max	Units
$R_{th(j-c)}$	Thermal resistance (per arm)	Continuous dissipation – junction to case	-	-	48	°C/kW
$R_{th(c-h)}$	Thermal resistance – case to heatsink (per module)	Mounting torque 5Nm (with mounting grease)	-	-	6	°C/kW
T_j	Junction temperature		-40	-	150	°C
T_{stg}	Storage temperature range		-40	-	125	°C
	Screw Torque	Mounting – M6	-	-	5	Nm
		Electrical connections – M8	-	-	10	Nm

STATIC ELECTRICAL CHARACTERISTICS – PER ARM

T_{case} = 25°C unless stated otherwise.

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
I_{RM}	Peak reverse current	V_R = 3300V, T_j = 150°C			30	mA
V_F	Forward voltage	I_F = 500A		2.4		V
		I_F = 500A, T_j = 125°C		2.5		V
		I_F = 500A, T_j = 150°C		2.4		V
L_M	Inductance	-		25		nH

DYNAMIC ELECTRICAL CHARACTERISTICS – PER ARM

T_{case} = 25°C unless stated otherwise

Symbol	Parameter	Test Conditions	Min	Typ.	Max	Units
Q_{rr}	Reverse recovery charge	I_F = 500A V_R = 1800V dI_F/dt = 1400A/µs		285		µC
I_{rr}	Peak reverse recovery current			310		A
E_{rec}	Reverse recovery energy			335		mJ

T_{case} = 125°C unless stated otherwise

Symbol	Parameter	Test Conditions	Min	Typ.	Max	Units
Q_{rr}	Reverse recovery charge	I_F = 500A V_R = 1800V dI_F/dt = 1400A/µs		470		µC
I_{rr}	Peak reverse recovery current			390		A
E_{rec}	Reverse recovery energy			570		mJ

T_{case} = 150°C unless stated otherwise

Symbol	Parameter	Test Conditions	Min	Typ.	Max	Units
Q_{rr}	Reverse recovery charge	I_F = 500A V_R = 1800V dI_F/dt = 1400A/µs		535		µC
I_{rr}	Peak reverse recovery current			400		A
E_{rec}	Reverse recovery energy			650		mJ

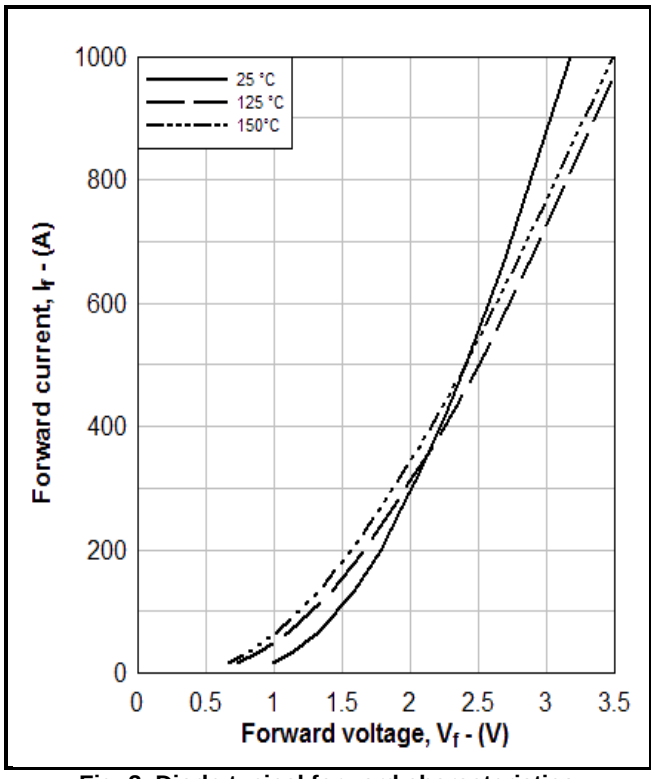


Fig. 3 Diode typical forward characteristics

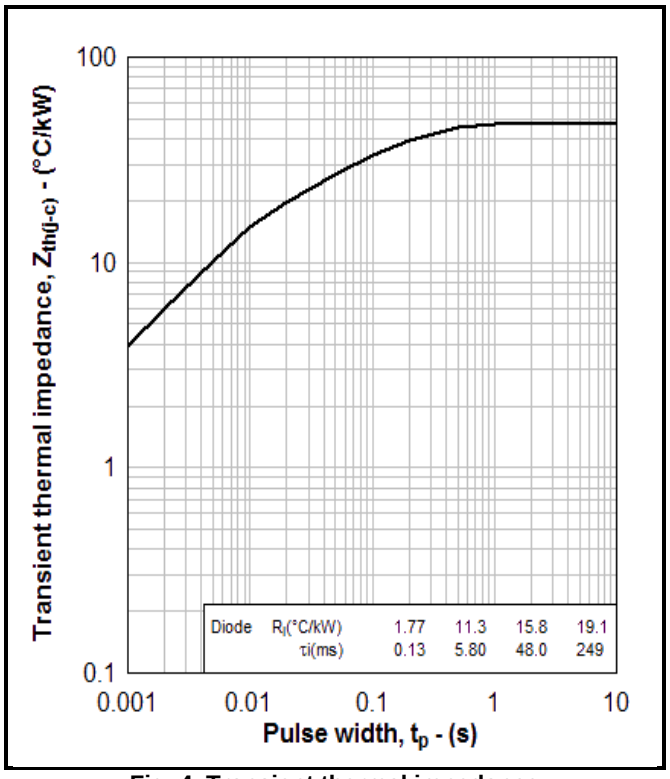


Fig. 4 Transient thermal impedance

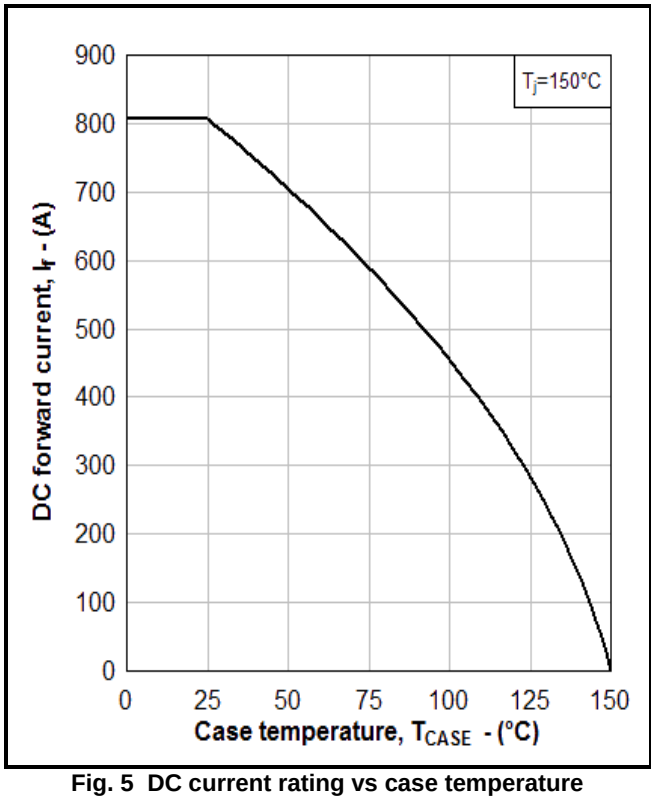


Fig. 5 DC current rating vs case temperature

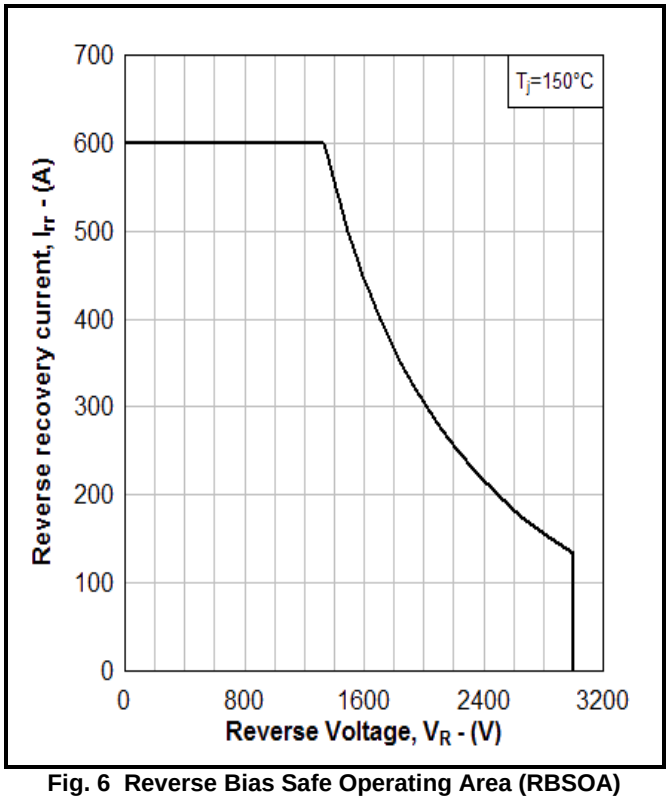
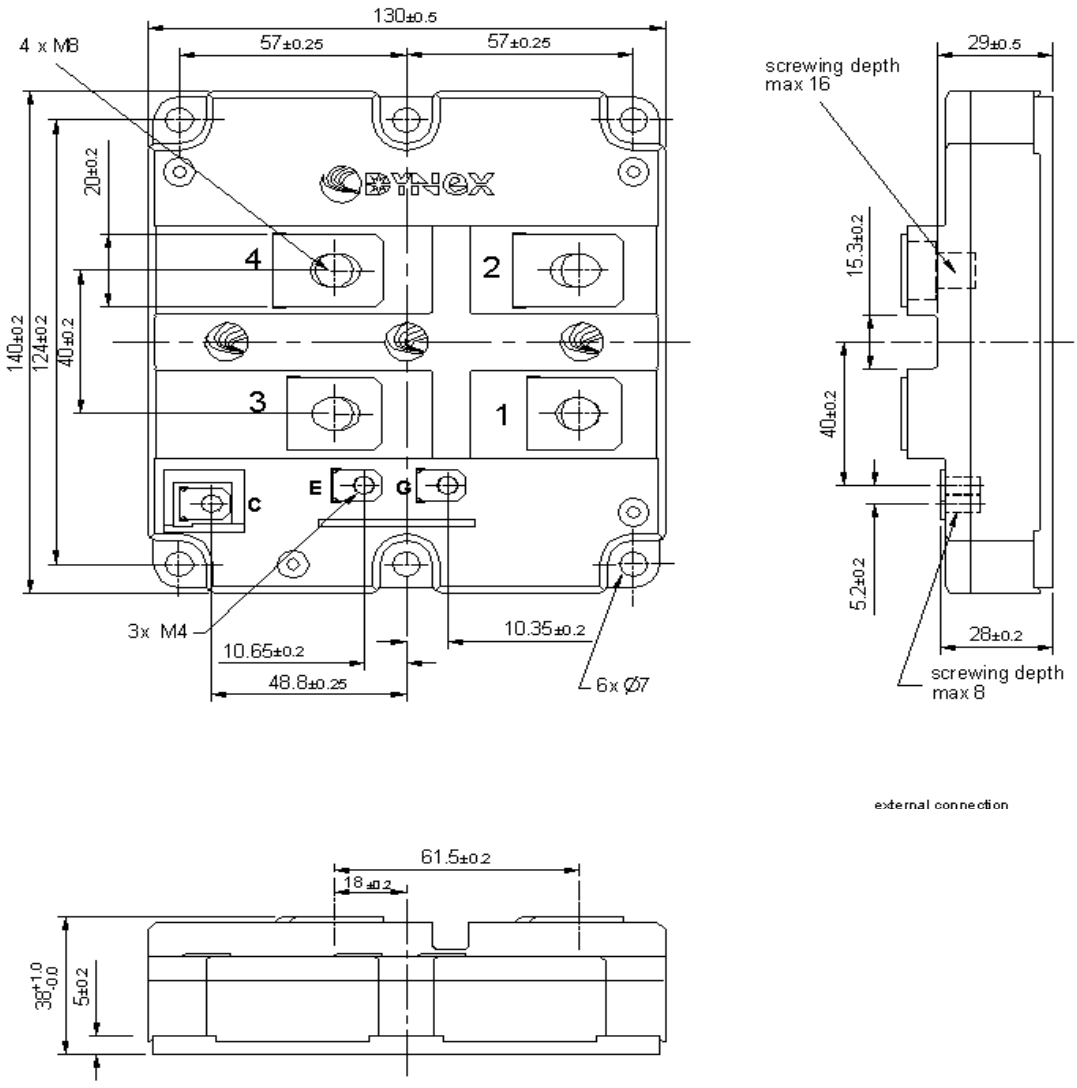


Fig. 6 Reverse Bias Safe Operating Area (RBSOA)

PACKAGE DETAILS

For further package information, please visit our website or contact Customer Services.
All dimensions in mm, unless stated otherwise.
DO NOT SCALE.



Nominal Weight: 900g

Module Outline Type Code: N

Fig. 7 Module outline drawing

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